

Edited by
Margrit Hanbücken,
Pierre Müller,
and Ralf B. Wehrspohn

**Mechanical Stress
on the Nanoscale**

Related Titles

Alkauskas, A., Deák, P., Neugebauer, J.,
Pasquarello, A., Van de Walle, C. G. (eds.)

Advanced Calculations for Defects in Materials

Electronic Structure Methods

402 pages with 118 figures

2011

Hardcover

ISBN: 978-3-527-41024-8

Jackson, K. A.

Kinetic Processes

**Crystal Growth, Diffusion, and
Phase Transitions in Materials**

453 pages with 291 figures

2010

Hardcover

ISBN: 978-3-527-32736-2

Stallinga, P.

Electrical Characterization of Organic Electronic Materials and Devices

316 pages

2009

Hardcover

ISBN: 978-0-470-75009-4

Zehetbauer, M. J., Zhu, Y. T. (eds.)

Bulk Nanostructured Materials

736 pages with 366 figures and 31 tables

2009

Hardcover

ISBN: 978-3-527-31524-6

Cazacu, O. (ed.)

Multiscale Modeling of Heterogenous Materials

**From Microstructure to Macro-Scale
Properties**

343 pages

2008

Hardcover

ISBN: 978-1-84821-047-9

Birkholz, M.

Thin Film Analysis by X-Ray Scattering

**Sharing the Planet's Freshwater
Resources**

378 pages with 175 figures and 28 tables

2006

Hardcover

ISBN: 978-3-527-31052-4

Edited by
Margrit Hanbücken, Pierre Müller, and Ralf B. Wehrspohn

Mechanical Stress on the Nanoscale

Simulation, Material Systems and Characterization
Techniques



WILEY-VCH Verlag GmbH & Co. KGaA

The Editors

Dr. Margrit Hanbücken

CINaM-CNRS
Campus Luminy
Marseille, Frankreich

Dr. Pierre Müller

Université Paul Cézanne
Campus Saint-Jérôme
Marseille, Frankreich

Prof. Dr. Ralf B. Wehrspohn

Fraunhofer Inst. für
Werkstoffmechanik Halle
Halle, Germany

All books published by Wiley-VCH are carefully produced. Nevertheless, authors, editors, and publisher do not warrant the information contained in these books, including this book, to be free of errors. Readers are advised to keep in mind that statements, data, illustrations, procedural details or other items may inadvertently be inaccurate.

Library of Congress Card No.: applied for

British Library Cataloguing-in-Publication Data

A catalogue record for this book is available from the British Library.

Bibliographic information published by the Deutsche Nationalbibliothek

The Deutsche Nationalbibliothek lists this publication in the Deutsche Nationalbibliografie; detailed bibliographic data are available on the Internet at <http://dnb.d-nb.de>.

© 2011 Wiley-VCH Verlag & Co. KGaA,
Boschstr. 12, 69469 Weinheim, Germany

All rights reserved (including those of translation into other languages). No part of this book may be reproduced in any form – by photoprinting, microfilm, or any other means – nor transmitted or translated into a machine language without written permission from the publishers. Registered names, trademarks, etc. used in this book, even when not specifically marked as such, are not to be considered unprotected by law.

Typesetting Thomson Digital, Noida, India

Printing

Binding

Cover Design Grafik-Design Schulz, Fußgönheim

Printed in Singapore

Printed on acid-free paper

Print ISBN: 978-3-527-41066-8

ePDF ISBN: 978-3-527-63956-4

oBook ISBN: 978-3-527-63954-0

ePub ISBN: 978-3-527-63955-7

Contents

Preface *XV*

List of Contributors *XVII*

Part One Fundamentals of Stress and Strain on the Nanoscale 1

1	Elastic Strain Relaxation: Thermodynamics and Kinetics	3
	<i>Frank Glas</i>	
1.1	Basics of Elastic Strain Relaxation	3
1.1.1	Introduction	3
1.1.2	Principles of Calculation	4
1.1.3	Methods of Calculation: A Brief Overview	6
1.2	Elastic Strain Relaxation in Inhomogeneous Substitutional Alloys	7
1.2.1	Spinodal Decomposition with No Elastic Effects	8
1.2.2	Elastic Strain Relaxation in an Alloy with Modulated Composition	9
1.2.3	Strain Stabilization and the Effect of Elastic Anisotropy	11
1.2.4	Elastic Relaxation in the Presence of a Free Surface	11
1.3	Diffusion	12
1.3.1	Diffusion without Elastic Effects	12
1.3.2	Diffusion under Stress in an Alloy	13
1.4	Strain Relaxation in Homogeneous Mismatched Epitaxial Layers	14
1.4.1	Introduction	14
1.4.2	Elastic Strain Relaxation	15
1.4.3	Critical Thickness	16
1.5	Morphological Relaxation of a Solid under Nonhydrostatic Stress	17
1.5.1	Introduction	17
1.5.2	Calculation of the Elastic Relaxation Fields	18
1.5.3	ATG Instability	19
1.5.4	Kinetics of the ATG Instability	21
1.5.5	Coupling between the Morphological and Compositional Instabilities	21
1.6	Elastic Relaxation of 0D and 1D Epitaxial Nanostructures	22
1.6.1	Quantum Dots	23

1.6.2	Nanowires	24
	References	24

2 Fundamentals of Stress and Strain at the Nanoscale Level: Toward Nanoelasticity 27

Pierre Müller

2.1	Introduction	27
2.2	Theoretical Background	28
2.2.1	Bulk Elasticity: A Recall	28
2.2.1.1	Stress and Strain Definition	29
2.2.1.2	Equilibrium State	29
2.2.1.3	Elastic Energy	30
2.2.1.4	Elastic Constants	30
2.2.2	How to Describe Surfaces or Interfaces?	31
2.2.3	Surfaces and Interfaces Described from Excess Quantities	34
2.2.3.1	The Surface Elastic Energy as an Excess of the Bulk Elastic Energy	34
2.2.3.2	The Surface Stress and Surface Strain Concepts	35
2.2.3.3	Surface Elastic Constants	37
2.2.3.4	Connecting Surface and Bulk Stresses	39
2.2.3.5	Surface Stress and Surface Tension	40
2.2.3.6	Surface Stress and Adsorption	41
2.2.3.7	The Case of Glissile Interfaces	42
2.2.4	Surfaces and Interfaces Described as a Foreign Material	42
2.2.4.1	The Surface as a Thin Bulk-Like Film	43
2.2.4.2	The Surface as an Elastic Membrane	43
2.3	Applications: Size Effects Due to the Surfaces	44
2.3.1	Lattice Contraction of Nanoparticles	44
2.3.2	Effective Modulus of Thin Freestanding Plane Films	46
2.3.3	Bending, Buckling, and Free Vibrations of Thin Films	48
2.3.3.1	General Equations	48
2.3.3.2	Discussion	50
2.3.4	Static Bending of Nanowires: An Analysis of the Recent Literature	52
2.3.4.1	Young Modulus versus Size: Two-Phase Model	52
2.3.4.2	Young Modulus versus Size: Surface Stress Model	53
2.3.4.3	Prestress Bulk Due to Surface Stresses	53
2.3.5	A Short Overview of Experimental Difficulties	54
2.4	Conclusion	55
	References	56

3 Onset of Plasticity in Crystalline Nanomaterials 61

Laurent Pizzagalli, Sandrine Brochard, and Julien Godet

3.1	Introduction	61
3.2	The Role of Dislocations	63

3.3	Driving Forces for Dislocations	63
3.3.1	Stress	64
3.3.2	Thermal Activation	64
3.3.3	Combination of Stress and Thermal Activation	64
3.4	Dislocation and Surfaces: Basic Concepts	65
3.4.1	Forces Related to Surface	65
3.4.2	Balance of Forces for Nucleation	66
3.4.3	Forces Due to Lattice Friction	66
3.4.4	Surface Modifications Due to Dislocations	68
3.5	Elastic Modeling	68
3.5.1	Elastic Model	68
3.5.2	Predicted Activation Parameters	70
3.5.3	What is Missing?	70
3.5.4	Peierls–Nabarro Approaches	72
3.6	Atomistic Modeling	72
3.6.1	Examples of Simulations	73
3.6.2	Determination of Activation Parameters	74
3.6.3	Comparison with Experiments	75
3.6.4	Influence of Surface Structure, Orientation, and Chemistry	76
3.7	Extension to Different Geometries	78
3.8	Discussion	79
	References	80
4	Relaxations on the Nanoscale: An Atomistic View by Numerical Simulations	83
	<i>Christine Mottet</i>	
4.1	Introduction	84
4.2	Theoretical Models and Numerical Simulations	85
4.2.1	Energetic Models	85
4.2.2	Numerical Simulations	87
4.2.3	Definitions of Physical Quantities	89
4.3	Relaxations in Surfaces and Interfaces	91
4.3.1	Surface Reconstructions	92
4.3.2	Surface Alloys: a Simple Case of Heteroatomic Adsorption	94
4.3.3	Heteroepitaxial Thin Films	96
4.4	Relaxations in Nanoclusters	98
4.4.1	Free Nanoclusters	99
4.4.2	Supported Nanoclusters	100
4.4.3	Nanoalloys	101
4.5	Conclusions	103
	References	104

Part Two Model Systems with Stress-Engineered Properties 107

- 5 Accommodation of Lattice Misfit in Semiconductor Heterostructure Nanowires 109**
Volker Schmidt and Joerg V. Wittemann
- 5.1 Introduction 109
- 5.2 Dislocations in Axial Heterostructure Nanowires 111
- 5.3 Dislocations in Core–Shell Heterostructure Nanowires 113
- 5.4 Roughening of Core–Shell Heterostructure Nanowires 115
- 5.4.1 Zeroth-Order Stress and Strain 117
- 5.4.2 First-Order Contribution to Stress and Strain 120
- 5.4.3 Linear Stability Analysis 122
- 5.4.4 Results and Discussion 124
- 5.5 Conclusion 127
- References 127
- 6 Strained Silicon Nanodevices 131**
Manfred Reiche, Oussama Moutanabbir, Jan Hoentschel, Angelika Hähnel, Stefan Flachowsky, Ulrich Gösele, and Manfred Horstmann
- 6.1 Introduction 131
- 6.2 Impact of Strain on the Electronic Properties of Silicon 132
- 6.3 Methods to Generate Strain in Silicon Devices 135
- 6.3.1 Substrates for Nanoscale CMOS Technologies 135
- 6.3.2 Local Strain 136
- 6.3.3 Global Strain 139
- 6.3.3.1 Biaxially Strained Layers 139
- 6.3.3.2 Uniaxially Strained Layers 142
- 6.4 Strain Engineering for 22 nm CMOS Technologies and Below 142
- 6.5 Conclusions 146
- References 146
- 7 Stress-Driven Nanopatterning in Metallic Systems 151**
Vincent Repain, Sylvie Rousset, and Shobhana Narasimhan
- 7.1 Introduction 151
- 7.2 Surface Stress as a Driving Force for Patterning at Nanometer Length Scales 152
- 7.2.1 Surface Stress 152
- 7.2.2 Surface Reconstruction and Misfit Dislocations 153
- 7.2.2.1 Homoepitaxial Surfaces 153
- 7.2.2.2 Heteroepitaxial Systems 155
- 7.2.3 Stress Domains 156

7.2.4	Vicinal Surfaces	157
7.3	Nanopatterned Surfaces as Templates for the Ordered Growth of Functionalized Nanostructures	158
7.3.1	Metallic Ordered Growth on Nanopatterned Surface	158
7.3.1.1	Introduction	158
7.3.1.2	Nucleation and Growth Concepts	159
7.3.1.3	Heterogeneous Growth	160
7.4	Stress Relaxation by the Formation of Surface-Confined Alloys	162
7.4.1	Two-Component Systems	162
7.4.2	Three-Component Systems	162
7.5	Conclusion	164
	References	165
8	Semiconductor Templates for the Fabrication of Nano-Objects	169
	<i>Joël Eymery, Laurence Masson, Houda Sahaf, and Margrit Hanbücken</i>	
8.1	Introduction	169
8.2	Semiconductor Template Fabrication	170
8.2.1	Artificially Prepatterned Substrates	170
8.2.1.1	Morphological Patterning	170
8.2.1.2	Silicon Etched Stripes: Example of the Use of Strain to Control Nanostructure Formation and Physical Properties	171
8.2.1.3	Use of Buried Stressors	171
8.2.2	Patterning through Vicinal Surfaces	173
8.2.2.1	Generalities	173
8.2.2.2	Vicinal Si(111)	173
8.2.2.3	Vicinal Si(100)	173
8.3	Ordered Growth of Nano-Objects	175
8.3.1	Growth Modes and Self-Organization	175
8.3.2	Quantum Dots and Nanoparticles Self-Organization with Control in Size and Position	176
8.3.2.1	Stranski–Krastanov Growth Mode	176
8.3.2.2	Au/Si(111) System	177
8.3.2.3	Ge/Si(001) System	179
8.3.3	Wires: Catalytic and Catalyst-Free Growths with Control in Size and Position	179
8.3.3.1	Strain in Bottom-Up Wire Heterostructures: Longitudinal and Radial Heterostructures	181
8.3.3.2	Wires as a Position Controlled Template	183
8.4	Conclusions	184
	References	184

Part Three Characterization Techniques of Measuring Stresses on the Nanoscale 189

9	Strain Analysis in Transmission Electron Microscopy: How Far Can We Go? 191
	<i>Anne Ponchet, Christophe Gatel, Christian Roucau, and Marie-José Casanove</i>
9.1	Introduction: How to Get Quantitative Information on Strain from TEM 192
9.1.1	Displacement, Strain, and Stress in Elasticity Theory 192
9.1.2	Principles of TEM and Application to Strained Nanosystems 192
9.1.3	A Major Issue for Strained Nanostructure Analysis: The Thin Foil Effect 193
9.2	Bending Effects in Nanometric Strained Layers: A Tool for Probing Stress 194
9.2.1	Bending: A Relaxation Mechanism 194
9.2.2	Relation between Curvature and Internal Stress 195
9.2.3	Using the Bending as a Probe of the Epitaxial Stress: The TEM Curvature Method 196
9.2.4	Occurrence of Large Displacements in TEM Thinned Samples 197
9.2.5	Advantages and Limits of Bending as a Probe of Stress in TEM 199
9.3	Strain Analysis and Surface Relaxation in Electron Diffraction 199
9.3.1	CBED: Principle and Application to Determination of Lattice Parameters 199
9.3.2	Strain Determination in CBED 201
9.3.3	Use and Limitations of CBED in Strain Determination 202
9.3.4	Nanobeam Electron Diffraction 203
9.4	Strain Analysis from HREM Image Analysis: Problematic of Very Thin Foils 203
9.4.1	Principle 203
9.4.2	What Do We Really Measure in an HREM Image? 205
9.4.2.1	Image Formation 205
9.4.2.2	Reconstruction of the 3D Strain Field from a 2D Projection 205
9.4.3	Modeling the Surface Relaxation in an HREM Experiment 206
9.4.3.1	Full Relaxation (Uniaxial Stress) 206
9.4.3.2	Intermediate Situations: Usefulness of Finite Element Modeling 207
9.4.3.3	Thin Foil Effect: A Source of Incertitude in HREM 207
9.4.4	Conclusion: HREM is a Powerful but Delicate Method of Strain Analysis 208
9.5	Conclusions 209
	References 210

10	Determination of Elastic Strains Using Electron Backscatter Diffraction in the Scanning Electron Microscope	213
	<i>Michael Krause, Matthias Petzold, and Ralf B. Wehrspohn</i>	
10.1	Introduction	213
10.2	Generation of Electron Backscatter Diffraction Patterns	214
10.3	Strain Determination Through Lattice Parameter Measurement	215
10.4	Strain Determination Through Pattern Shift Measurement	216
10.4.1	Linking Pattern Shifts to Strain	216
10.4.2	Measurement of Pattern Shifts	219
10.5	Sampling Strategies: Sources of Errors	221
10.6	Resolution Considerations	222
10.7	Illustrative Application	225
10.8	Conclusions	229
	References	230
11	X-Ray Diffraction Analysis of Elastic Strains at the Nanoscale	233
	<i>Olivier Thomas, Odile Robach, Stéphanie Escoubas, Jean-Sébastien Micha, Nicolas Vaxelaire, and Olivier Perroud</i>	
11.1	Introduction	233
11.2	Strain Field from Intensity Maps around Bragg Peaks	234
11.3	Average Strains from Diffraction Peak Shift	236
11.4	Local Strains Using Submicrometer Beams and Scanning XRD	240
11.4.1	Introduction	240
11.4.2	High-Energy Monochromatic Beam: 3DXRD	241
11.4.3	White Beam: Laue Microdiffraction	243
11.5	Local Strains Derived from the Intensity Distribution in Reciprocal Space	248
11.5.1	Periodic Assemblies of Identical Objects with Coherence Length > Few Periods	248
11.5.1.1	Introduction	248
11.5.1.2	Reciprocal Space Mapping	249
11.5.1.3	Applications	251
11.5.2	Single-Object Coherent Diffraction	252
11.6	Phase Retrieval from Strained Crystals	254
11.7	Conclusions and Perspectives	255
	References	256
12	Diffuse X-Ray Scattering at Low-Dimensional Structures in the System SiGe/Si	259
	<i>Michael Hanke</i>	
12.1	Introduction	259
12.2	Self-Organized Growth of Mesoscopic Structures	259
12.2.1	The Stranski–Krastanow Process	260
12.2.2	LPE-Grown Si _{1-x} Ge _x /Si(001) Islands	261

12.3	X-Ray Scattering Techniques	262
12.3.1	High-Resolution X-Ray Diffraction	262
12.3.2	Grazing Incidence Diffraction	263
12.3.3	Grazing Incidence Small-Angle X-Ray Scattering	264
12.4	Data Evaluation	265
12.5	Results	266
12.5.1	The Influence of Shape and Size on the GISAXS Signal	266
12.5.2	HRXRD Measurement of Strain and Composition	269
12.5.3	Positional Correlation Effects in HRXRD	270
12.5.4	Iso-Strain Scattering	271
12.6	Summary	273
	References	274
13	Direct Measurement of Elastic Displacement Modes by Grazing Incidence X-Ray Diffraction	275
	<i>Geoffroy Prévot</i>	
13.1	Introduction	275
13.2	Elastic Displacement Modes: Analysis and GIXD Observation	276
13.2.1	Fundamentals of Linear Elasticity in Direct Space	276
13.2.1.1	Basic Equations	276
13.2.1.2	Atomic Displacements and Elastic Interactions	277
13.2.2	Green's Tensor in Reciprocal Space	279
13.2.3	Grazing Incidence X-Ray Diffraction of Elastic Modes	280
13.2.3.1	Diffraction by a Surface	280
13.2.3.2	Contribution of the Elastic Modes	280
13.2.3.3	Procedure for Analyzing the Systems	281
13.3	Self-Organized Surfaces	282
13.3.1	Force Distribution and Interaction Energy for Self-Organized Surfaces	282
13.3.2	A 1D Case: OCu(110)	283
13.3.3	A 2D Case: NCu(001)	286
13.4	Vicinal Surfaces	289
13.4.1	Force Distribution and Interaction Energy for Steps	289
13.4.2	Experimental Results for Vicinal Surfaces of Transition Metals	292
13.5	Conclusion	294
	References	295
14	Submicrometer-Scale Characterization of Solar Silicon by Raman Spectroscopy	299
	<i>Michael Becker, George Sarau, and Silke Christiansen</i>	
14.1	Introduction	299
14.2	Crystal Orientation	300
14.2.1	Qualitative Maps	300
14.2.2	Quantitative Analysis	302

14.2.3	Comparison with Other Orientation Measurement Methods	306
14.3	Analysis of Stress and Strain States	307
14.3.1	General Theoretical Description	307
14.3.2	Quantitative Strain/Stress Analysis in Polycrystalline Silicon Wafers	309
14.3.2.1	Assumptions	309
14.3.2.2	Numerical Determination of Stress Components	310
14.3.3	Experimental Procedure to Determine Phonon Frequency Shifts	311
14.3.4	Additional Influences on the Phonon Frequency Shifts	311
14.3.4.1	Temperature	311
14.3.4.2	Drift of the Spectrometer Grating	313
14.3.5	Applications	313
14.3.5.1	Mechanical Stresses at the Backside of Silicon Solar Cells	313
14.3.5.2	Stress Fields at Microcracks in Polycrystalline Silicon Wafers	315
14.3.5.3	Stress States at Grain Boundaries in Polycrystalline Silicon Solar Cell Material and the Relation to the Grain Boundary Microstructure and Electrical Activity	316
14.3.6	Comparison with other Stress/Strain Measurement Methods	318
14.4	Measurement of Free Carrier Concentrations	318
14.4.1	Theoretical Description	319
14.4.2	Experimental Details	321
14.4.2.1	Small-Angle Beveling and Nomarski Differential Interference Contrast Micrographs	321
14.4.2.2	Evaluation of the Raman Data	322
14.4.2.3	Calibration Measurements	324
14.4.3	Experimental Results	324
14.4.4	Comparison with other Dopant Measurement Methods	328
14.5	Concluding Remarks	328
	References	329
15	Strain-Induced Nonlinear Optics in Silicon	333
	<i>Clemens Schrieffer, Christian Bohley, and Ralf B. Wehrspohn</i>	
15.1	Introduction	333
15.2	Fundamentals of Second Harmonic Generation in Nonlinear Optical Materials	334
15.3	Second Harmonic Generation and Its Relation to Structural Symmetry	336
15.3.1	Sources of Second Harmonic Signals	337
15.3.2	Bulk Contribution to Second Harmonic Generation	338
15.3.3	Surface Contribution to Second Harmonic Generation	341
15.4	Strain-Induced Modification of Second-Order Nonlinear Susceptibility in Silicon	343

15.5	Strained Silicon in Integrated Optics	348
15.5.1	Strain-Induced Electro-Optical Effect	348
15.5.2	Strain-Induced Photoelastic Effect	350
15.6	Conclusions	352
	References	353

Index	357
--------------	-----

Preface

The development of future integrated (“smart”) micro- and nanosystems is generally focusing on further improvements of functionality and performance, enhancement of miniaturization and integration density, and extension into new application fields. In addition to any of these technological developments, reliability, quality, and manufacturing yield are key prerequisites for the development of any complex innovative (“smart”) micro-/nanosystem application. Consequently, new methods, instruments, and tools adjusted to the specific boundary conditions of the miniaturization level down to the nanoscale have to be provided allowing the investigation and understanding of the microstructure, possible failure processes, and reliability risks. In addition, methods and tools allowing the addressing and measurement of locally affected material properties, such as residual stresses, in combination with the microstructure are required. Such instruments and techniques are required to support a focused and rapid technological development and the time-efficient design of components and smart systems.

The particular results of microstructure and stress characterization do not only provide the basis for technological process step improvement but are also required for advanced simulation approaches and models that can be used to consider reliability properties already during the product development stage (“design for reliability” concept). Such concepts gain increasing importance since they allow to reduce time-to-market and development cost.

Present local stress and strain measurements on the nanoscale are based on special transmission electron microscopy techniques such as CBED, HRTEM-GPA, or holographic dark field technology, special scanning electron microscopy techniques such as EBSD or adapted X-ray diffraction techniques such as coherent X-ray diffraction. This book brings together leading groups in these different disciplines to apply these techniques for local strain and stress measurement and its theoretical background.

The book consists of three parts. Part One addresses the fundamentals of stress and strain on the nanoscale including an introduction to thermodynamics, kinetics, and models of elasticity, plasticity, and relaxation. Part Two addresses applications where stress and strain on the nanoscale are relevant such as SiGe devices or nanowires. In Part Three, techniques for measuring stress and strain on the

nanoscale are presented such as CBED-TEM, EBSD-REM, different ways to use X-rays, Raman, and nonlinear optical methods.

To our knowledge, it is for the first time that this compendium combines theory, measurement techniques, and applications for stress and strain on the nanoscale. We believe that with increasing complexity of nanoscale devices, the increasing amount of the integration of various technologies, and various aspect ratios, it will be crucial to understand in detail processes and phenomena of nanostress.

This work was stimulated by the cooperation of the Fraunhofer Society, the Max-Planck-Society, the Carnot Association, and the CNRS via the C’Nano-PACA.

This book is dedicated to Prof. Ulrich Gösele, who cointiated this project.

February 28, 2011
Halle and Marseille

Ralf Wehrspohn
Margrit Hanbücken
Pierre Müller

List of Contributors

Michael Becker

Max Planck Institute of
Microstructure Physics
Experimental Department II
Weinberg 2
06120 Halle
Germany

Sandrine Brochard

Institut PPRIME – CNRS UPR 3346
Département de Physique et de
Mécanique des Matériaux
Espace Phymat, BP 30179
86962 Futuroscope Chasseneuil Cedex
France

Christian Bohley

Martin-Luther-University
Institute of Physics
Heinrich-Damerow – Str. 4
06120 Halle
Germany

and

Martin-Luther-University
Centre for Innovation Competence
SiLi-nano
Karl-Freiherr-von-Fritsch-Str. 3
06120 Halle (Saale), Germany

Marie-José Casanove

CNRS-UPS
Centre d'Elaboration de Matériaux
et d'Etudes Structurales
29, rue Jeanne Marvig, BP 94347
31055 Toulouse Cedex 4
France

Silke Christiansen

Max Planck Institute for
the Science of Light
Guenther-Scharowsky – Str. 1
91058 Erlangen
Germany

Stéphanie Escoubas

Aix-Marseille Université
IM2NP, Faculté des Sciences
et Techniques
Campus de Saint-Jérôme
Avenue Escadrille Normandie
Niemen, Case 142
13397 Marseille Cedex
France

and

CNRS, IM2NP (UMR 6242)
Faculté des Sciences et Techniques
Campus de Saint-Jérôme
Avenue Escadrille Normandie Niemen,
Case 142
13397 Marseille Cedex
France

Joël Eymery

CEA/CNRS/Université Joseph Fourier
CEA, INAC, SP2M
17 rue des Martyrs
38054 Grenoble Cedex 9
France

Stefan Flachowsky

GLOBALFOUNDRIES Fab 1
Wilschdorfer Landstraße 101
01109 Dresden
Germany

Christophe Gatel

CNRS-UPS
Centre d'Elaboration de Matériaux
et d'Etudes Structurales
29, rue Jeanne Marvig, BP 94347
31055 Toulouse Cedex 4
France

Frank Glas

CNRS
Laboratoire de Photonique et de
Nanostructures
Route de Nozay
91460 Marcoussis
France

Julien Godet

Institut PPRIME – CNRS UPR 3346
Département de Physique et de
Mécanique des Matériaux
Espace Phymat, BP 30179
86962 Futuroscope Chasseneuil Cedex
France

Ulrich Gösele[†]

Max Planck Institute of
Microstructure Physics
Weinberg 2
06120 Halle
Germany

Angelika Hähnel

Max Planck Institute of
Microstructure Physics
Weinberg 2
06120 Halle
Germany

Margrit Hanbücken

CINaM-CNRS
Campus de Luminy, Case 913
3288 Marseille Cedex 9
France

Michael Hanke

Paul-Drude-Institute for Solid State
Electronics
Hausvogteiplatz 5-7
10117 Berlin
Germany

Jan Hoentschel

GLOBALFOUNDRIES Fab 1
Wilschdorfer Landstraße 101
01109 Dresden
Germany

Manfred Horstmann

GLOBALFOUNDRIES Fab 1
Wilschdorfer Landstraße 101
01109 Dresden
Germany

Michael Krause

Fraunhofer IWM
Walter-Hülse – Str. 1
06120 Halle
Germany

Laurence Masson

CINaM-CNRS
Campus de Luminy, Case 913
3288 Marseille Cedex 9
France

Jean-Sébastien Micha

INAC/SPrAM
 UMR 5819 (CEA-CNRS-UJF)
 CEA-Grenoble
 17 rue des Martyrs
 38054 Grenoble Cedex 9
 France

Christine Mottet

CINaM – CNRS
 Campus de Luminy, Case 913
 13288 Marseille Cedex 9
 France

Oussama Moutanabbir

Max Planck Institute of
 Microstructure Physics
 Weinberg 2
 06120 Halle
 Germany

Pierre Müller

Aix Marseille Université
 Center Interdisciplinaire de
 Nanoscience de Marseille
 UPR CNRS 3118
 Campus de Luminy, Case 913
 13288 Marseille Cedex 9
 France

Shobhana Narasimhan

JNCASR
 Theoretical Sciences Unit
 Jakkur
 560 064 Bangalore
 India

Olivier Perroud

Aix-Marseille Université
 IM2NP, Faculté des Sciences
 et Techniques
 Campus de Saint-Jérôme
 Avenue Escadrille Normandie
 Niemen, Case 142
 13397 Marseille Cedex
 France

and

CNRS, IM2NP (UMR 6242)
 Faculté des Sciences et Techniques
 Campus de Saint-Jérôme
 Avenue Escadrille Normandie Niemen,
 Case 142
 13397 Marseille Cedex
 France

Laurent Pizzagalli

Institut PPRIME – CNRS UPR 3346
 Département de Physique et de
 Mécanique des Matériaux
 Espace Phymat, BP 30179
 86962 Futuroscope Chasseneuil Cedex
 France

Anne Ponchet

CNRS-UPS
 Centre d'Elaboration de Matériaux
 et d'Etudes Structurales
 29, rue Jeanne Marvig, BP 94347
 31055 Toulouse Cedex 4
 France

Matthias Petzold

Fraunhofer Institute for Mechanics
 of Materials Halle
 Walter-Hülse-Str.1
 06120 Halle

Geoffroy Prévot

Université Pierre et Marie Curie-Paris 6
UMR CNRS 7588, Institut des
NanoSciences de Paris
Campus Boucicaut, 140 rue de Lourmel
75015 Paris
France

Manfred Reiche

Max Planck Institute of
Microstructure Physics
Weinberg 2
06120 Halle
Germany

Vincent Repain

CNRS et Université Paris Diderot
Matériaux et Phénomènes Quantiques
Bâtiment Condorcet – Case 7021
75205 Paris
France

Odile Robach

CEA-Grenoble
INAC/SP2M/NRS
17 rue des Martyrs
38054 Grenoble Cedex 9
France

Christian Roucau

CNRS-UPS
Centre d'Elaboration de Matériaux
et d'Etudes Structurales
29, rue Jeanne Marvig, BP 94347
31055 Toulouse Cedex 4
France

Sylvie Rousset

CNRS et Université Paris Diderot
Matériaux et Phénomènes Quantiques
Bâtiment Condorcet – Case 7021
75205 Paris
France

Houda Sahaf

CINaM-CNRS
Campus de Luminy, Case 913
3288 Marseille Cedex 9
France

George Sarau

Max Planck Institute of Microstructure
Physics
Experimental Department II
Weinberg 2
06120 Halle
Germany

and

Max Planck Institute for
the Science of Light
Guenther-Scharowsky – Str. 1
91058 Erlangen
Germany

Volker Schmidt

Max Planck Institute of
Microstructure Physics
Experimental Department II
Weinberg 2
06120 Halle
Germany

Clemens Schrieber

Martin-Luther-University
Institute of Physics
Heinrich-Damerow – Str. 4
06120 Halle
Germany

and

Martin-Luther-University
Centre for Innovation Competence
SiLi-nano
Karl-Freiherr-von-Fritsch-Str. 3
06120 Halle (Saale), Germany

Olivier Thomas

Aix-Marseille Université
 IM2NP, Faculté des Sciences et
 Techniques
 Campus de Saint-Jérôme
 Avenue Escadrille Normandie Niemen,
 Case 142
 13397 Marseille Cedex
 France

and

CNRS, IM2NP (UMR 6242)
 Faculté des Sciences et Techniques
 Campus de Saint-Jérôme
 Avenue Escadrille Normandie Niemen,
 Case 142
 13397 Marseille Cedex
 France

Nicolas Vaxelaire

Aix-Marseille Université
 IM2NP, Faculté des Sciences et
 Techniques
 Campus de Saint-Jérôme
 Avenue Escadrille Normandie Niemen,
 Case 142
 13397 Marseille Cedex
 France

and

CNRS, IM2NP (UMR 6242)
 Faculté des Sciences et Techniques
 Campus de Saint-Jérôme
 Avenue Escadrille Normandie Niemen,
 Case 142
 13397 Marseille Cedex
 France

Ralf B. Wehrspohn

Martin-Luther-University
 Institute of Physics
 Heinrich-Damerow – Str. 4
 06120 Halle
 Germany

and

Fraunhofer Institute for Mechanics
 of Materials Halle
 Walter-Hülse-Str. 1
 06120 Halle
 Germany

Joerg V. Wittemann

Max Planck Institute of
 Microstructure Physics
 Experimental Department II
 Weinberg 2
 06120 Halle
 Germany